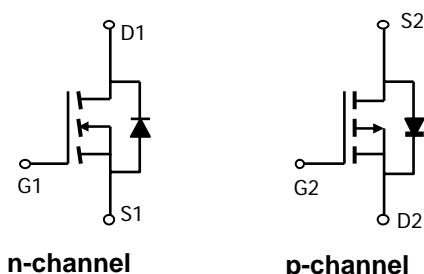
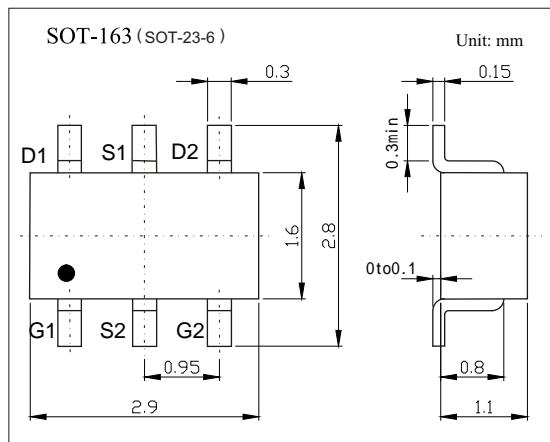


Dual Enhancement Mode MOSFET

APM2701CG

Features

N-Channel : $V_{DS}=20V$ $I_D=3A$ $R_{DS(ON)} < 70m\Omega$ ($V_{GS} = 4.5V$) $R_{DS(ON)} < 110m\Omega$ ($V_{GS} = 2.5V$)P-Channel : $V_{DS}=-20V$ $I_D=-1.5A$ $R_{DS(ON)} < 190m\Omega$ ($V_{GS} = -4.5V$) $R_{DS(ON)} < 235m\Omega$ ($V_{GS} = -2.5V$)Absolute Maximum Ratings $T_a = 25$

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	20	-20	V
Gate-Source Voltage	V_{GS}	± 10	± 10	
Continuous Drain Current	I_D	3	-1.5	A
Pulsed Drain Current	I_{DM}	10	-6	
Power Dissipation $T_a=25$	P_D	0.83		W
$T_a=100$		0.3		
Diode Continuous Forward Current	I_S	1	-1	A
Thermal Resistance.Junction- to-Ambient	R_{thJA}	150		/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		

APM2701CGElectrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Type	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250 \mu A, V_{GS}=0V$	N-CH	20			V	
		$I_D=-250 \mu A, V_{GS}=0V$	P-CH	-20				
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$	N-CH			1	μA	
		$V_{DS}=-16V, V_{GS}=0V$	P-CH			-1		
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V, V_{GS}= \pm 10V$	N-CH			± 100	nA	
		$V_{DS}=0V, V_{GS}= \pm 10V$	P-CH			± 100		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250 \mu A$	N-CH	0.45	0.6	1	V	
		$V_{DS}=V_{GS}, I_D=-250 \mu A$	P-CH	-0.45	-0.6	-1		
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=3A$	N-CH		50	70	m	
		$V_{GS}=2.5V, I_D=1.7A$			90	110		
		$V_{GS}=-4.5V, I_D=-1.5A$	P-CH		145	190		
		$V_{GS}=-2.5V, I_D=-1A$			180	2.35		
Input Capacitance	C_{iss}	N-Channel: $V_{GS}=0V, V_{DS}=10V, f=1MHz$	N-CH		270		pF	
Output Capacitance	C_{oss}		P-CH		300			
Reverse Transfer Capacitance	C_{rss}		N-CH		70			
			P-CH		50			
Total Gate Charge	Q_g	N-Channel: $V_{GS}=4.5V, V_{DS}=10V, I_D=3A$	N-CH		5	6.5	nC	
Gate Source Charge	Q_{gs}		P-CH		4	6		
Gate Drain Charge	Q_{gd}		N-CH		0.5			
			P-CH		0.6			
Turn-On Delay Time	$t_{d(on)}$		N-CH		1.6		ns	
Turn-On Rise Time	t_r		P-CH		1			
Turn-Off Delay Time	$t_{d(off)}$	N-Channel: $V_{GS}=4.5V, V_{DS}=10V, I_D=1A, R_{GEN}=6$ $RL=10$	N-CH		6	12	ns	
			P-CH		6	10		
Turn-Off Fall Time	t_f		N-CH		5	10		
			P-CH		8	12		
Diode Forward Voltage	V_{SD}	P-Channel: $V_{GS}=-4.5V, V_{DS}=-10V, I_D=-1A, R_{GEN}=6$ $RL=10$	N-CH		12	23		
			P-CH		10	15		
			N-CH		6	12		
			P-CH		5	10		
		$I_S=0.5A, V_{GS}=0V$	N-CH		0.7	1.3	V	
		$I_S=-0.5A, V_{GS}=0V$	P-CH		-0.7	-1.3		

■ Marking

Marking	52907
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